

201720070729007

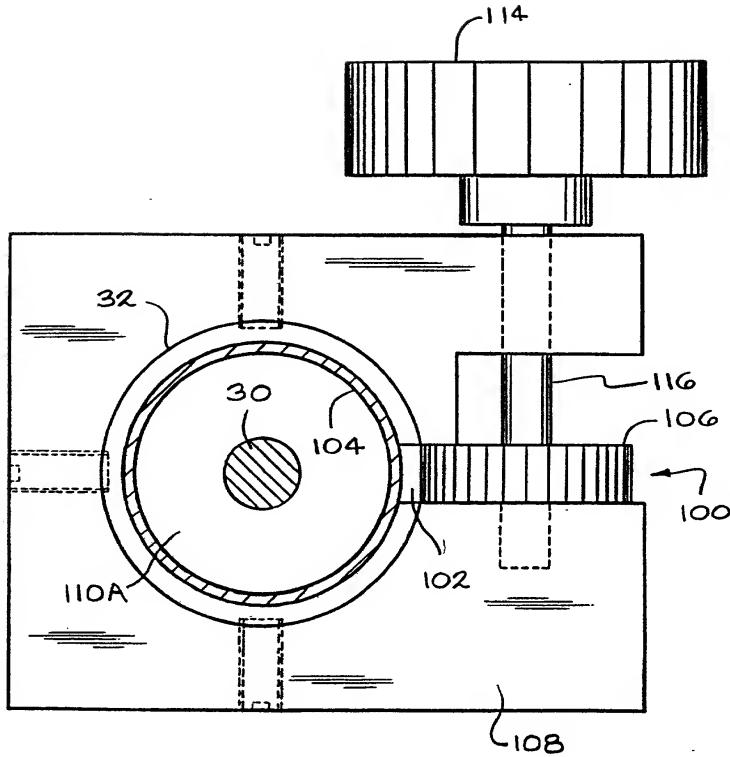
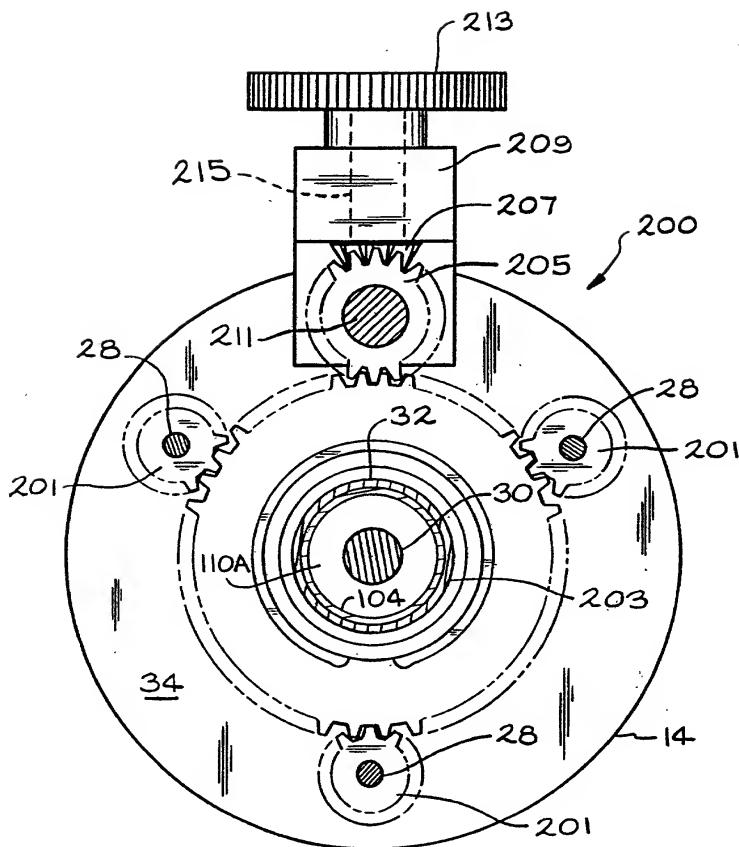


FIG. 1B



— FIG. 1C

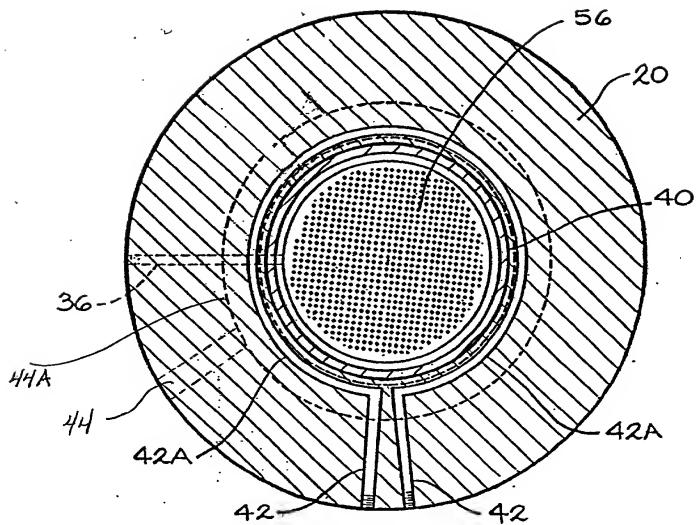


FIG. 1D

100073710.0024102

200073710, 07/2010

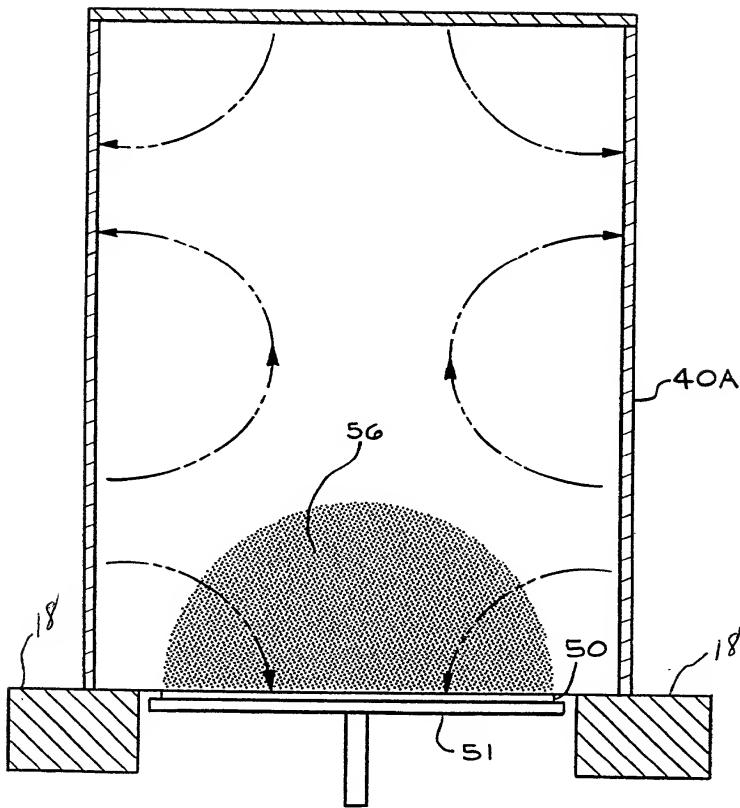


FIGURE 1E

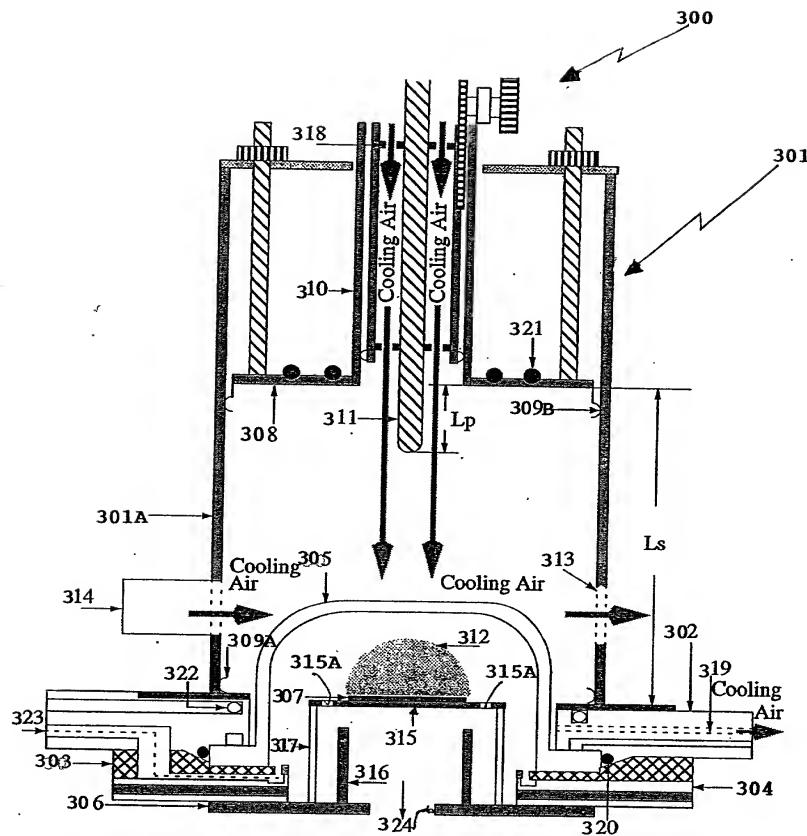


FIGURE 1F

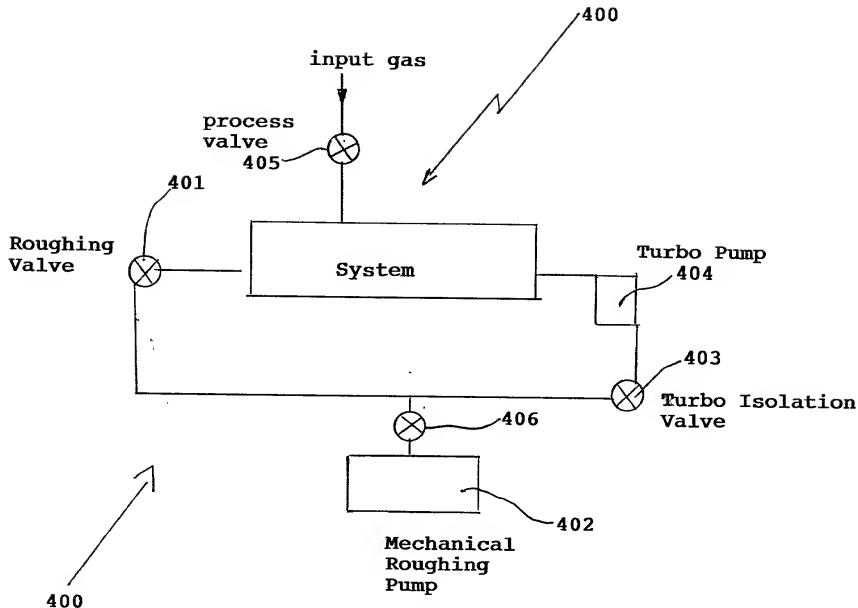


FIGURE 1G

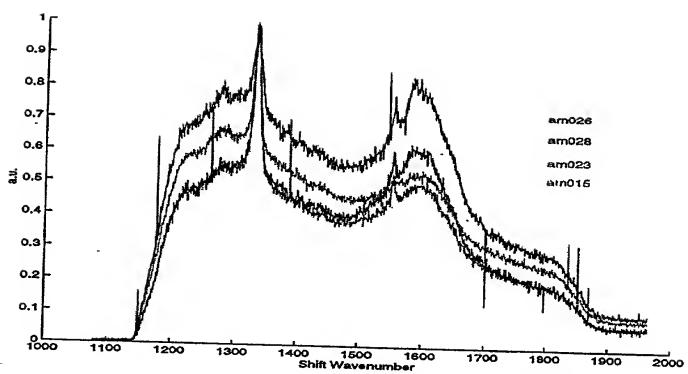


FIGURE 2

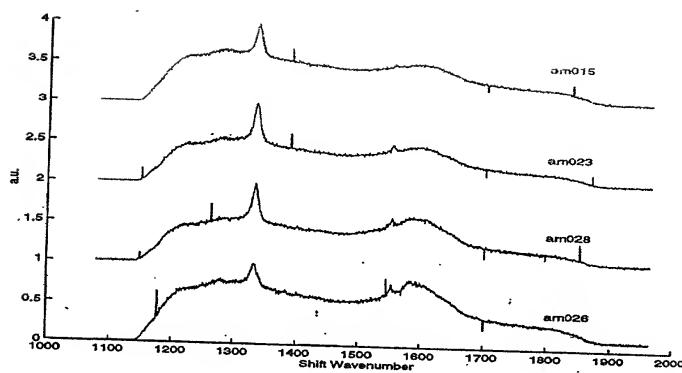


FIGURE 3

Pressure Investigation: Ar/H₂/CH₄=100/0/1 sccm

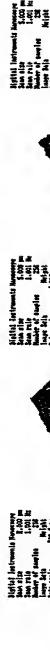


FIG. 4A
60 Torr, Img. RMS=33.322 nm,
growth=0.011 $\mu\text{m/hr}$

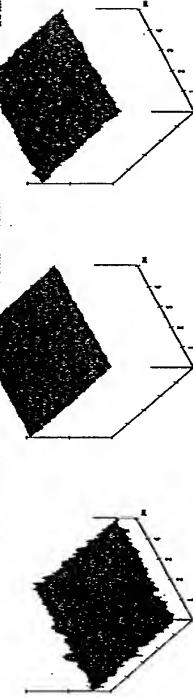


FIG. 4B
80 Torr, Img. RMS=22.696 nm,
growth=0.018 $\mu\text{m/hr}$

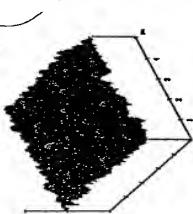


FIG. 4C
100 Torr, Img. RMS=19.151 nm,
growth=0.031 $\mu\text{m/hr}$

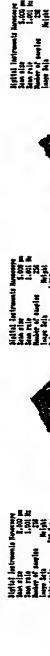


FIG. 4D
120 Torr, Img. RMS=10.859 nm,
growth=0.129 $\mu\text{m/hr}$

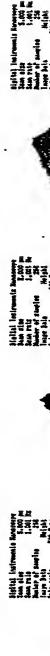


FIG. 4E
140 Torr, Img. RMS=13.584 nm,
growth=0.231 $\mu\text{m/hr}$

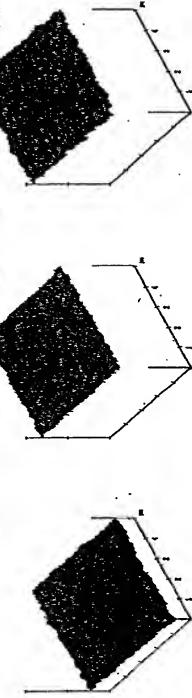


FIG. 4F
160 Torr, Img. RMS=13.462 nm,
growth=0.311 $\mu\text{m/hr}$

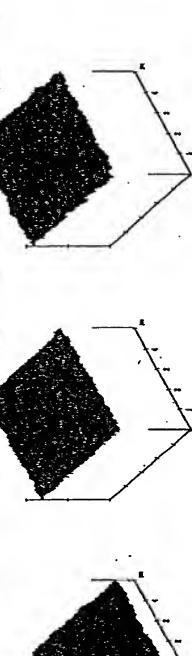


FIG. 4G
180 Torr, Img. RMS=16.782 nm,
growth=0.296 $\mu\text{m/hr}$

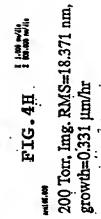
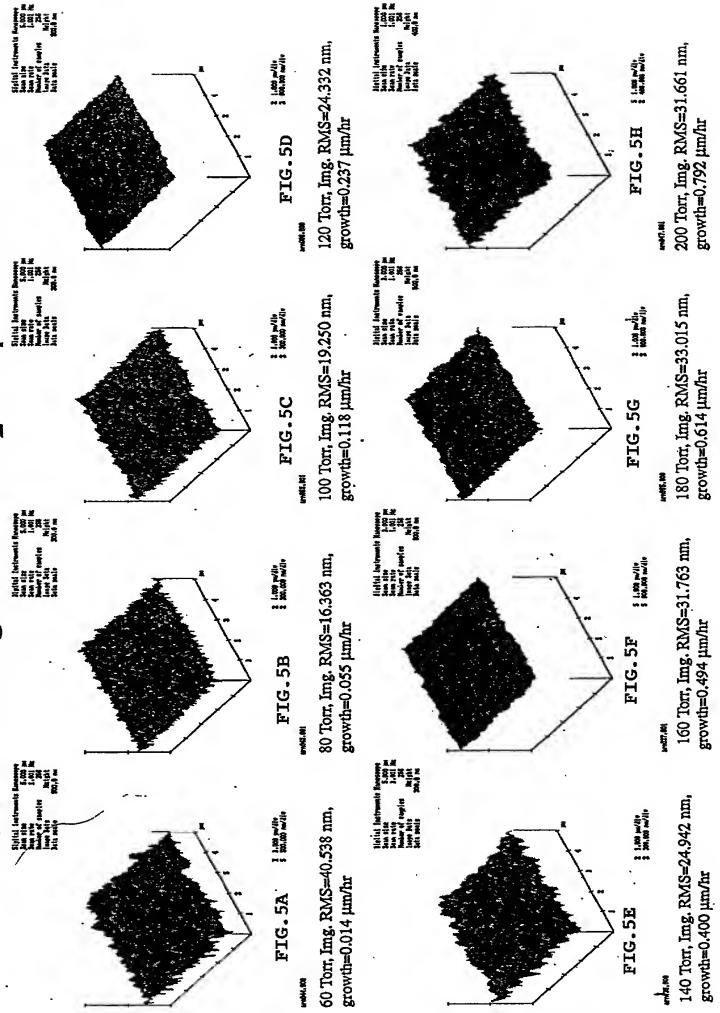


FIG. 4H
200 Torr, Img. RMS=18.371 nm,
growth=0.331 $\mu\text{m/hr}$

Pressure Investigation: Ar/H₂/CH₄=100/4/1 sccm



H₂ Concentration Variation: P=120Torr

Initial instrument parameters
Date: 10/10/2017
Time: 10:45:00 AM
Tool: 1000/1
Process: 1000/1
Power: 1000W
Ar flow: 100 sccm
H₂ flow: 100 sccm
O₂ flow: 0 sccm
N₂ flow: 0 sccm
CH₄ flow: 0 sccm
RF power: 1000W
Bias voltage: 0V
Growth rate: 0.337 μm/hr

Ar/H₂/CH₄=100/10/1, Img. RMS=40.961 nm,
growth=0.337 μm/hr

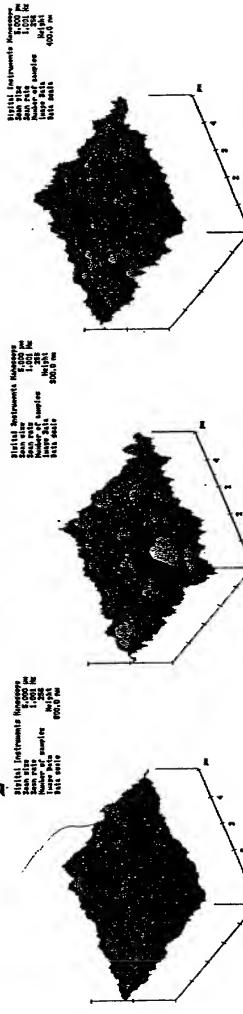


FIG. 6A

Ar/H₂/CH₄=100/8/1, Img. RMS=31.818 nm,
growth=0.328 μm/hr

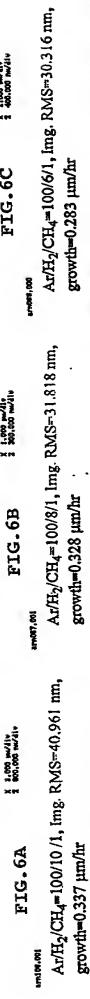


FIG. 6B

Ar/H₂/CH₄=100/6/1, Img. RMS=30.316 nm,
growth=0.283 μm/hr



FIG. 6C

Initial instrument parameters
Date: 10/10/2017
Time: 10:45:00 AM
Tool: 1000/1
Process: 1000/1
Power: 1000W
Ar flow: 100 sccm
H₂ flow: 100 sccm
O₂ flow: 0 sccm
N₂ flow: 0 sccm
CH₄ flow: 0 sccm
RF power: 1000W
Bias voltage: 0V
Growth rate: 0.172 μm/hr



FIG. 6D

Ar/H₂/CH₄=100/4/1,
Img. RMS=24.332 nm,
growth=0.237 μm/hr



FIG. 6E

Initial instrument parameters
Date: 10/10/2017
Time: 10:45:00 AM
Tool: 1000/1
Process: 1000/1
Power: 1000W
Ar flow: 100 sccm
H₂ flow: 100 sccm
O₂ flow: 0 sccm
N₂ flow: 0 sccm
CH₄ flow: 0 sccm
RF power: 1000W
Bias voltage: 0V
Growth rate: 0.148 μm/hr



FIG. 6F

Initial instrument parameters
Date: 10/10/2017
Time: 10:45:00 AM
Tool: 1000/1
Process: 1000/1
Power: 1000W
Ar flow: 100 sccm
H₂ flow: 100 sccm
O₂ flow: 0 sccm
N₂ flow: 0 sccm
CH₄ flow: 0 sccm
RF power: 1000W
Bias voltage: 0V
Growth rate: 0.129 μm/hr



FIG. 6G

N₂ Impurity Study: P=120Torr, Ar/H₂/CH₄=100/4/1 sccm

Initial Instruments Parameters
Base pressure: 1000 mPa
Growth rate: 1000 nm/hr
Growth time: 1000 sec
Growth temp: 1000 °C
Growth env: N₂

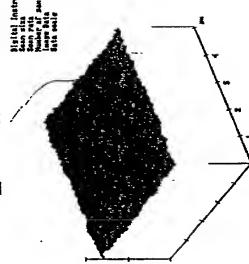


FIG. 7A
5ppm N, Img. RMS=24.332 nm,
growth=0.237 $\mu\text{m}/\text{hr}$

Initial Instruments Parameters
Base pressure: 1000 mPa
Growth rate: 1000 nm/hr
Growth time: 1000 sec
Growth temp: 1000 °C
Growth env: N₂

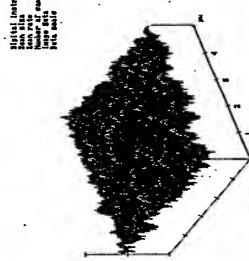


FIG. 7B
300ppm N, Img. RMS=20.447 nm,
growth=0.211 $\mu\text{m}/\text{hr}$

Initial Instruments Parameters
Base pressure: 1000 mPa
Growth rate: 1000 nm/hr
Growth time: 1000 sec
Growth temp: 1000 °C
Growth env: N₂

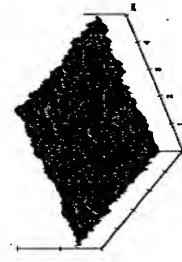


FIG. 7C
800ppm N, Img. RMS=20.808 nm,
growth=0.187 $\mu\text{m}/\text{hr}$

Initial Instruments Parameters
Base pressure: 1000 mPa
Growth rate: 1000 nm/hr
Growth time: 1000 sec
Growth temp: 1000 °C
Growth env: N₂

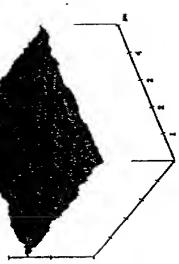


FIG. 7D
1500ppm N, Img. RMS=23.323 nm,
growth=0.164 $\mu\text{m}/\text{hr}$

Initial Instruments Parameters
Base pressure: 1000 mPa
Growth rate: 1000 nm/hr
Growth time: 1000 sec
Growth temp: 1000 °C
Growth env: N₂

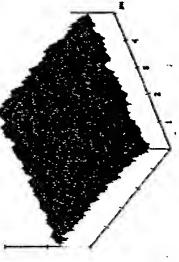


FIG. 7E
2000ppm N, Img. RMS=20.825 nm,
growth=0.147 $\mu\text{m}/\text{hr}$

Initial Instruments Parameters
Base pressure: 1000 mPa
Growth rate: 1000 nm/hr
Growth time: 1000 sec
Growth temp: 1000 °C
Growth env: N₂

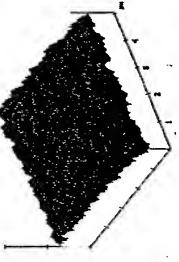


FIG. 7F
2500ppm N, Img. RMS=17.706 nm,
growth=0.147 $\mu\text{m}/\text{hr}$

Ar/H₂/CH₄ = 100/0/1 sccm

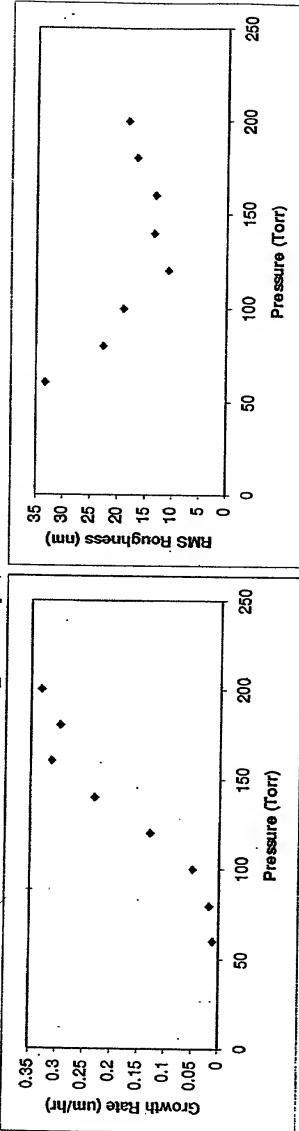


FIGURE 8

Ar/H₂/CH₄ = 100/4/1 sccm

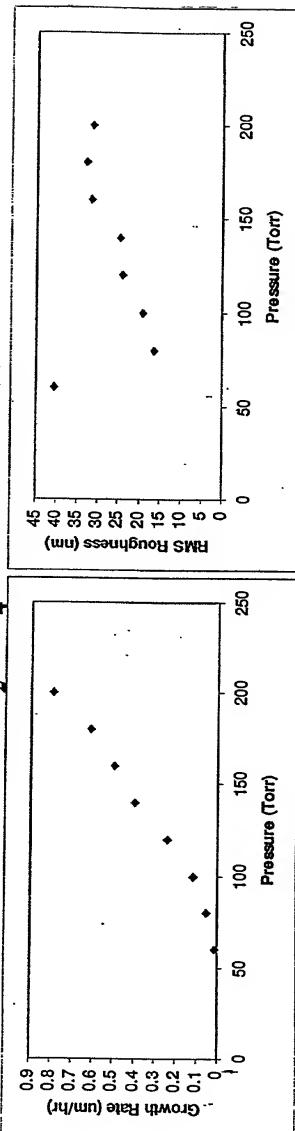


FIGURE 8A

FIGURE 9A

FIGURE 9

200 F220" DIFEZGOT

H₂ Concentration: 120 Torr

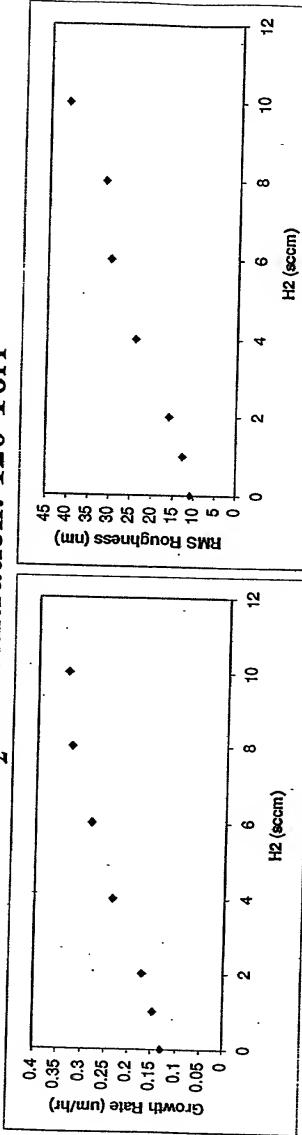


FIGURE 10

N₂ Impurity: P = 120 Torr, Ar/H₂/CH₄ = 100/4/1 sccm

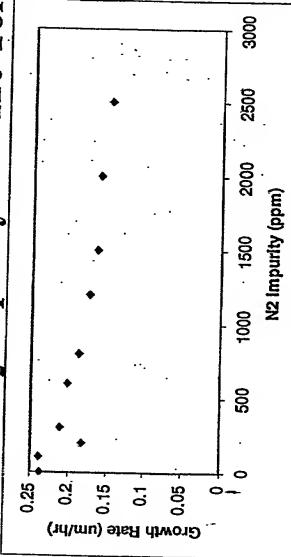


FIGURE 11

FIGURE 10A

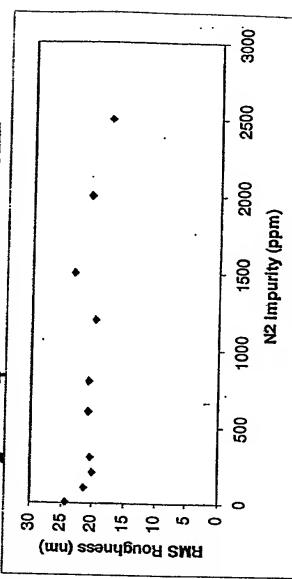
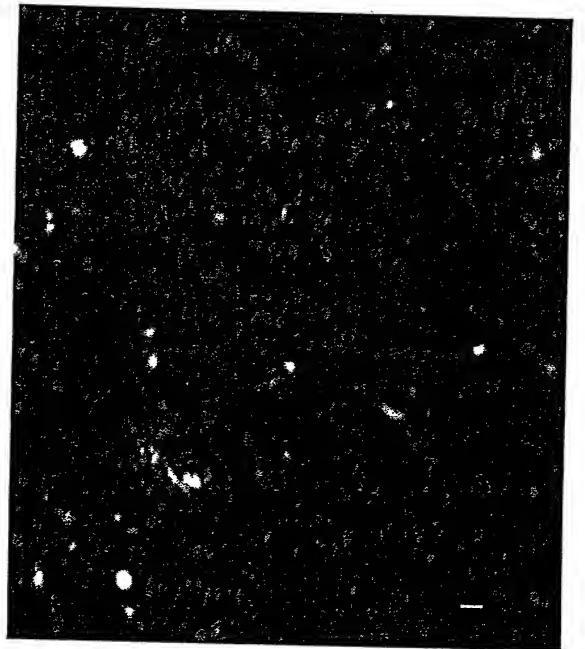


FIGURE 11A

200 kV - 0.072 EXPOSURE



— 10 nm

FIGURE 12

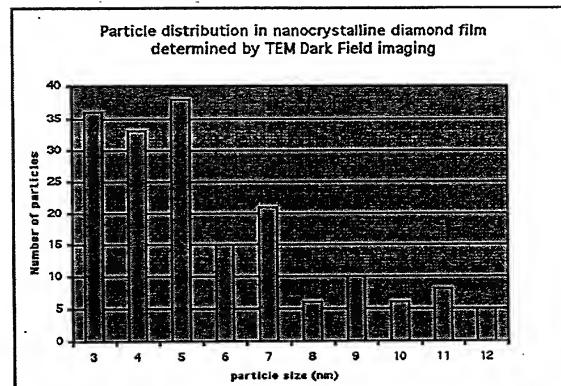


FIGURE 13

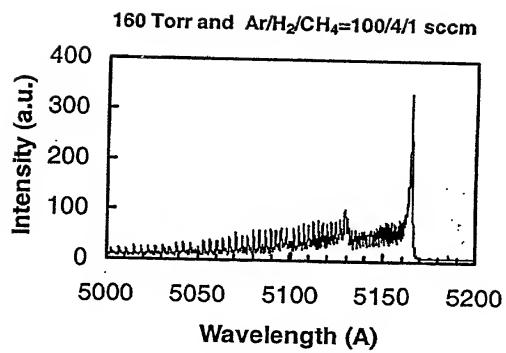


FIGURE 14

C₂ Rotational Temperature

Gas temperature versus pressure.

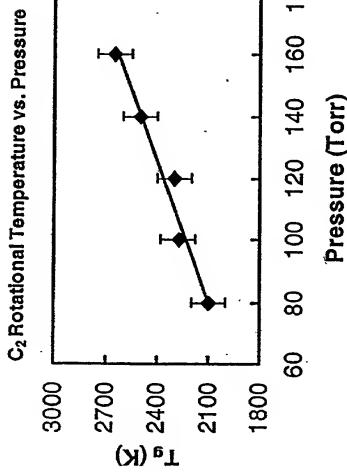


FIGURE 15

Gas temperature versus H₂ Flow.

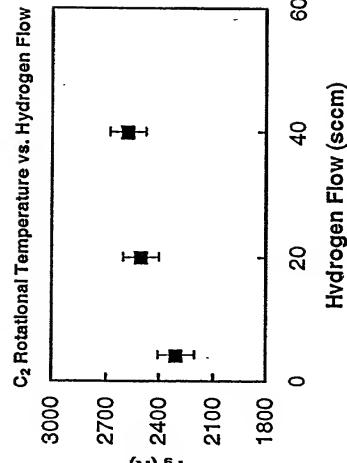


FIGURE 16

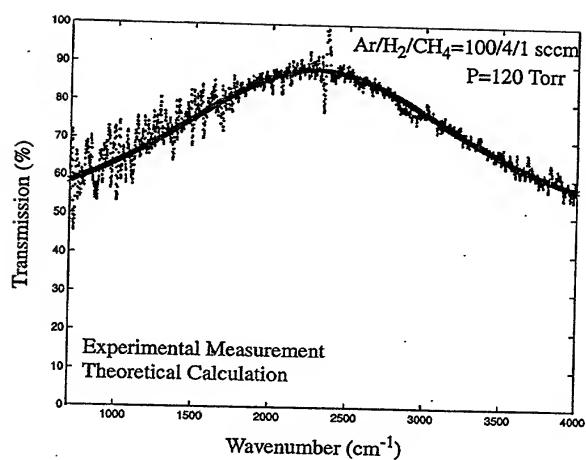


FIGURE 17

10023240 - 004402

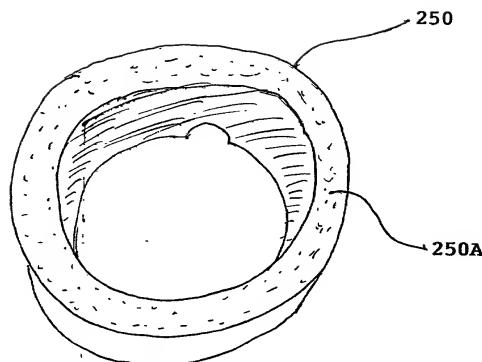


FIGURE 18

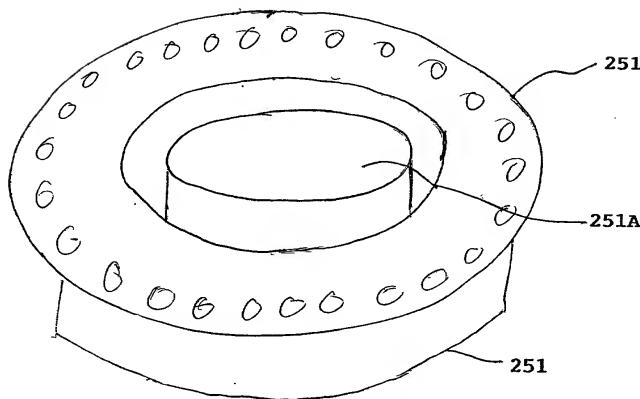


FIGURE 19

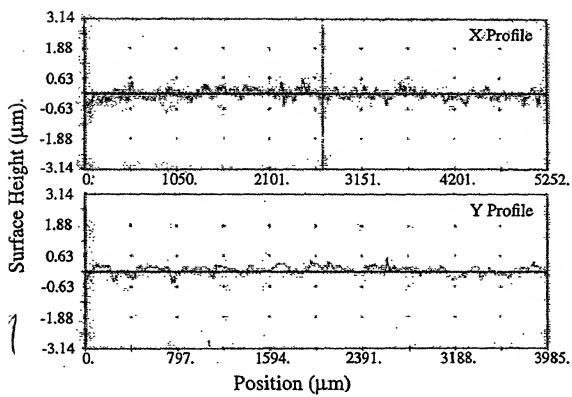


FIG. 20

FIG. 20A